

AQxxC-01FTG Series 450W Bidirectional TVS Diode

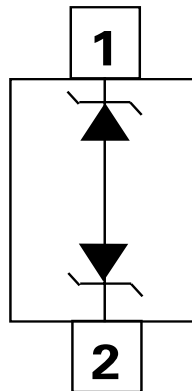


Description

The bidirectional AQxxC-01FTG Series is designed to replace multilayer varistors (MLVs) in electronic equipment for low speed and DC applications. It will protect any sensitive equipment from damage due to electrostatic discharge (ESD) and other transient events.

The AQxxC-01FTG series can safely absorb repetitive ESD strikes of ±30 kV (contact and air discharge as defined in IEC 61000-4-2) without any performance degradation. Additionally, the AQ05C can safely conduct a 30A 8/20 surge event as defined in IEC 61000-4-5 2nd Edition.

Pinout and Functional Block Diagram



Features

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 30A (8/20 as defined in IEC 61000-4-5 2nd edition) for the AQ05C
- Low clamping voltage
- PPAP capable
- Low leakage current
- Small SOD323 package fits 0805 footprints
- AEC-Q101 qualified
- Moisture Sensitivity Level(MSL -1)
- Halogen free, lead free and RoHS compliant

Applications

- Switches / Buttons
- Test Equipment / Instrumentation
- Point-of-Sale Terminals
- Medical Equipment
- Notebooks / Desktops / Servers
- Computer Peripherals
- CAN Bus protection
- Automotive applications

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
P_{pk}	Peak Pulse Power ($t_p=8/20\mu s$)	450	W
T_{OP}	Operating Temperature	-40 to 150	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

Notes:

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

AQ05C Electrical Characteristics ($T_{OP}=25^\circ C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R=1\mu A$			5.0	V
Breakdown Voltage	V_{BR}	$I_R=1mA$	6.0			V
Reverse Leakage Current	I_{LEAK}	$V_R=5V$			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A, t_p=8/20\mu s, Fwd$			10.0	V
		$I_{PP}=10A, t_p=8/20\mu s, Fwd$			14.5	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, I/O to Ground		0.31		Ω
Peak Pulse Current	I_{PP}	$t_p=8/20\mu s$			30.0	A
ESD Withstand Voltage ¹	V_{ESD}	IEC 61000-4-2 (Contact Discharge)	± 30			kV
		IEC 61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	$C_{I/O-I/O}$	Reverse Bias=0V, f=1MHz			200	pF

AQ12C Electrical Characteristics ($T_{OP}=25^\circ C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R=1\mu A$			12.0	V
Breakdown Voltage	V_{BR}	$I_R=1mA$	13.3			V
Reverse Leakage Current	I_{LEAK}	$V_R=12V$			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A, t_p=8/20\mu s, Fwd$			18.5	V
		$I_{PP}=10A, t_p=8/20\mu s, Fwd$			23.0	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, I/O to Ground		0.41		Ω
Peak Pulse Current	I_{PP}	$t_p=8/20\mu s$			17.0	A
ESD Withstand Voltage ¹	V_{ESD}	IEC 61000-4-2 (Contact Discharge)	± 30			kV
		IEC 61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	$C_{I/O-I/O}$	Reverse Bias=0V, f=1MHz			100	pF

AQ15C Electrical Characteristics (T_{op}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R =1μA			15.0	V
Breakdown Voltage	V _{BR}	I _R =1mA	16.7			V
Reverse Leakage Current	I _{LEAK}	V _R =15V			1.0	μA
Clamp Voltage ¹	V _C	I _{pp} =1A, t _p =8/20μs, Fwd			24.0	V
		I _{pp} =10A, t _p =8/20μs, Fwd			31.0	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, I/O to Ground		0.46		Ω
Peak Pulse Current	I _{pp}	t _p =8/20μs			12.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			75	pF

AQ24C Electrical Characteristics (T_{op}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R =1μA			24.0	V
Breakdown Voltage	V _{BR}	I _R =1mA	26.7			V
Reverse Leakage Current	I _{LEAK}	V _R =24V			1.0	μA
Clamp Voltage ¹	V _C	I _{pp} =1A, t _p =8/20μs, Fwd			36.0	V
		I _{pp} =5A, t _p =8/20μs, Fwd			42.0	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, I/O to Ground		0.62		Ω
Peak Pulse Current	I _{pp}	t _p =8/20μs			7.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			50	pF

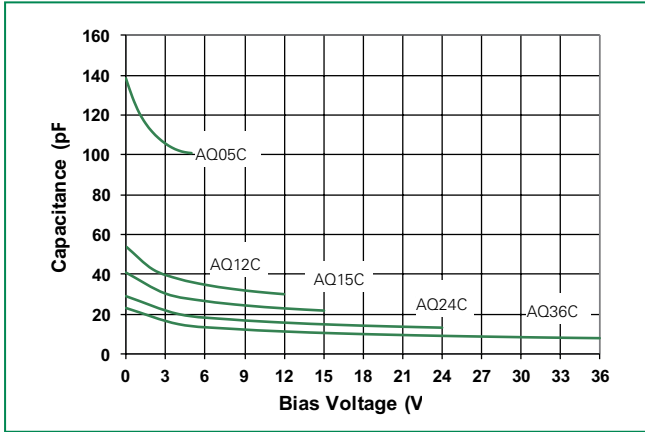
AQ36C Electrical Characteristics (T_{op}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R =1μA			36.0	V
Breakdown Voltage	V _{BR}	I _R =1mA	40.0			V
Reverse Leakage Current	I _{LEAK}	V _R =36V			1.0	μA
Clamp Voltage ¹	V _C	I _{pp} =1A, t _p =8/20μs, Fwd			52.0	V
		I _{pp} =5A, t _p =8/20μs, Fwd			62.0	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, I/O to Ground		0.68		Ω
Peak Pulse Current	I _{pp}	t _p =8/20μs			5.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			30	pF

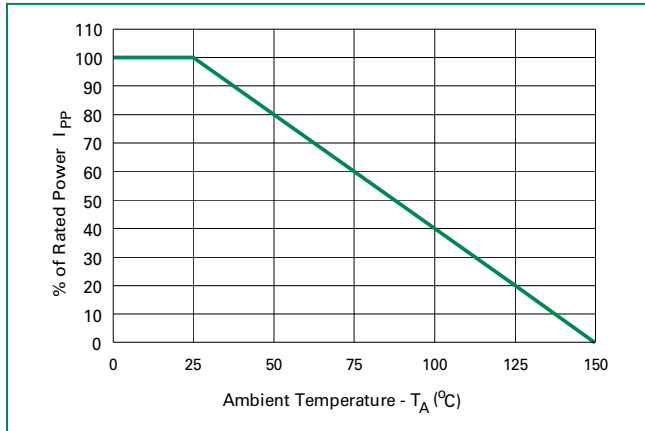
Note:

- Parameter is guaranteed by design and/or component characterization.
- Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2= 90ns

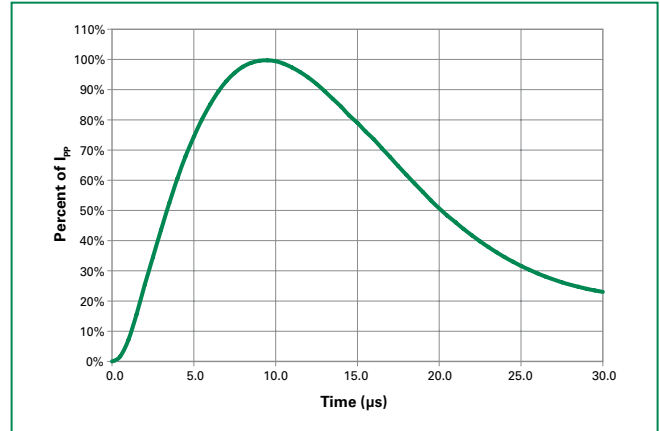
Capacitance vs. Bias



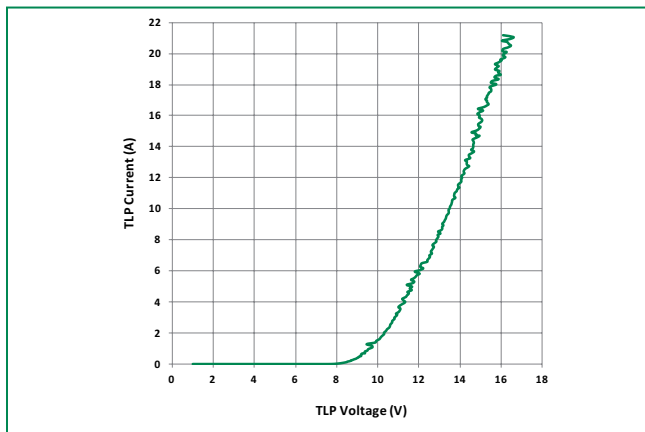
Power Derating Curve



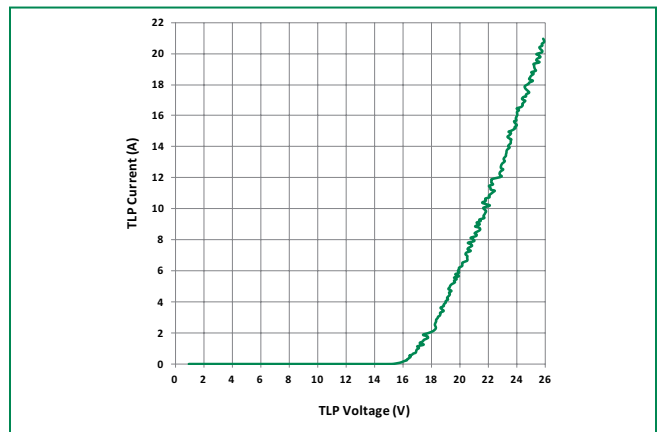
8/20µs Pulse Waveform



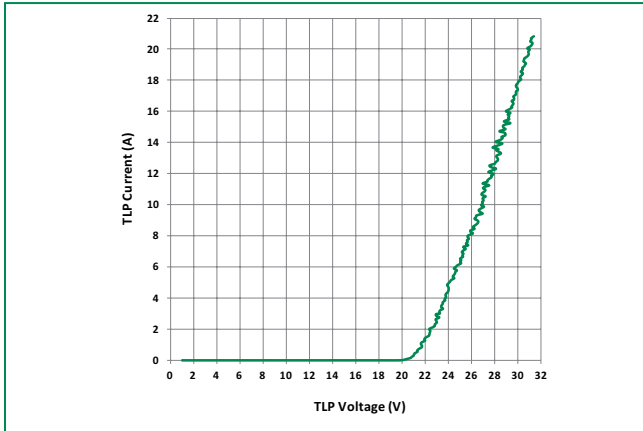
AQ05C Transmission Line Pulsing(TLP) Plot



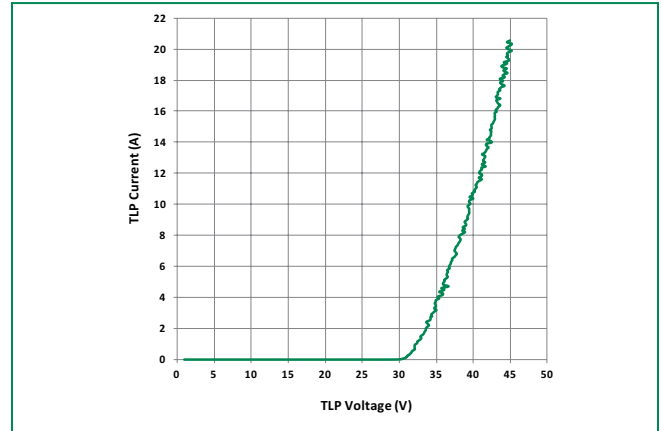
AQ12C Transmission Line Pulsing(TLP) Plot



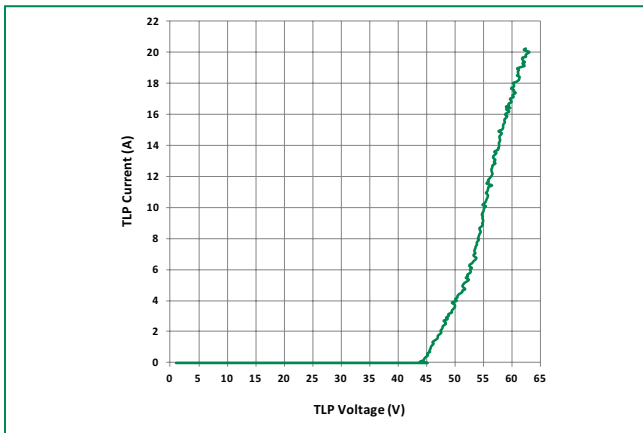
AQ15C Transmission Line Pulsing(TLP) Plot



AQ24C Transmission Line Pulsing(TLP) Plot



AQ36C Transmission Line Pulsing(TLP) Plot

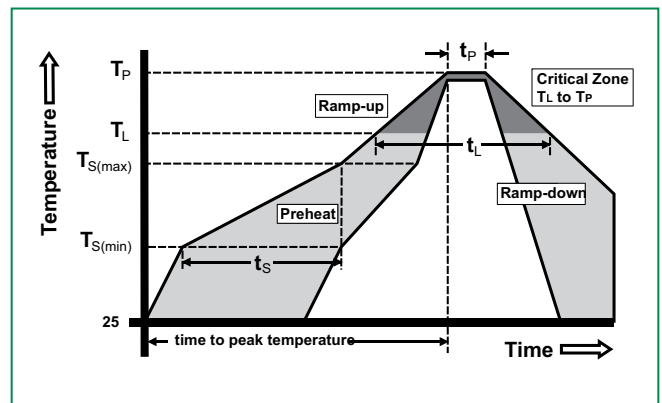


Product Characteristics

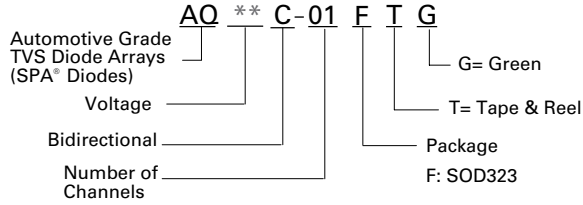
Lead Plating	Matte Tin
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Substrate material	Silicon
Body Material	Molded Compound
Flammability	UL Recognized compound meeting flammability rating V-0

Soldering Parameters

Reflow Condition	Pb – Free assembly	
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak	3°C/second max	
$T_{s(max)}$ to T_L - Ramp-up Rate	3°C/second max	
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)	260 ^{+0/-5} °C	
Time within 5°C of actual peak Temperature (t_p)	20 – 40 seconds	
Ramp-down Rate	6°C/second max	
Time 25°C to peak Temperature (T_p)	8 minutes Max.	
Do not exceed	260°C	



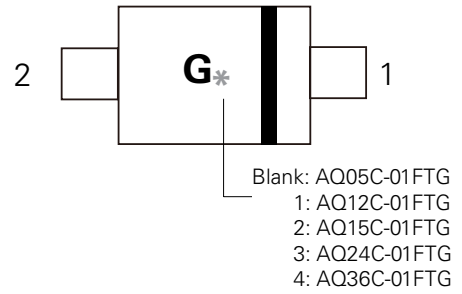
Part Numbering System



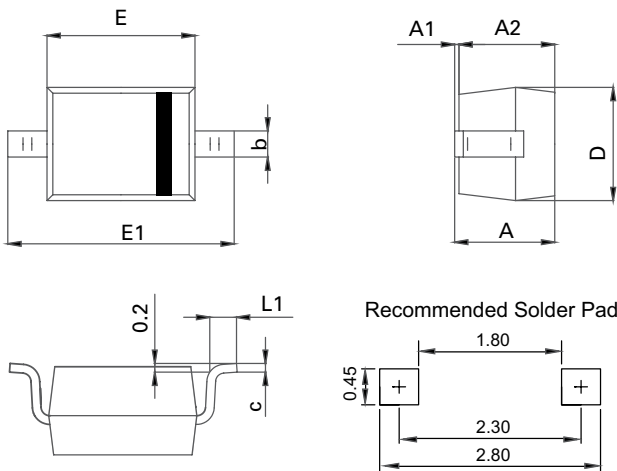
Ordering Information

Part Number	Package	Min. Order Qty.
AQ05C-01FTG	SOD323	3000
AQ12C-01FTG	SOD323	3000
AQ15C-01FTG	SOD323	3000
AQ24C-01FTG	SOD323	3000
AQ36C-01FTG	SOD323	3000

Part Marking System



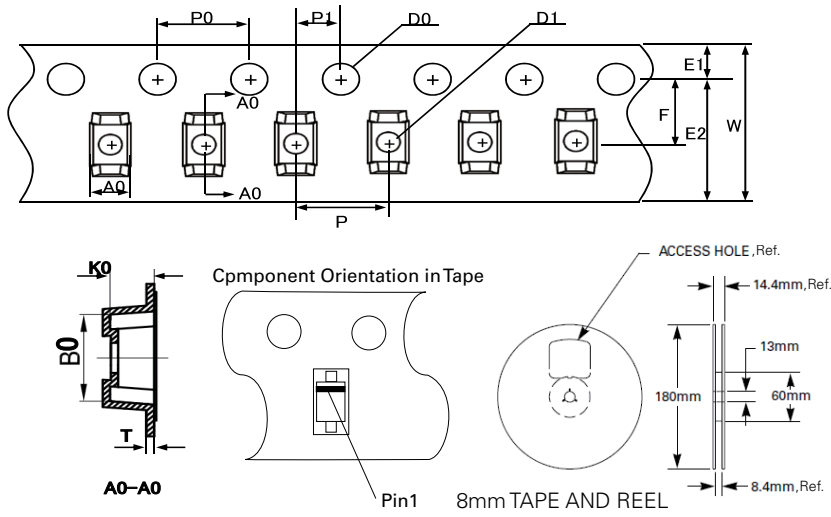
Package Dimensions -SOD323



Unit: mm

Symbol	SOD323			
	Millimeters		Inches	
	Min	Max	Min	Max
A	-	1.00	-	0.039
A1	0.00	0.10	0.000	0.004
A2	0.80	0.90	0.031	0.035
b	0.25	0.35	0.010	0.014
c	0.08	0.15	0.003	0.006
D	1.20	1.40	0.047	0.055
E	1.60	1.80	0.063	0.071
E1	2.50	2.70	0.098	0.106
L1	0.25	0.40	0.010	0.016

Embossed Carrier Tape & Reel Specification – SOD323



Symbol	Millimeters
A0	1.36min/1.62max
B0	2.90+/-0.10
W	8.0+0.3/-0.10
D0	1.50+0.10
D1	ø1.00min/ø1.25max
E	1.75+/-0.10
E2	-
F	3.50+/-0.05
P0	4.00+/-0.10
P	4.00+/-0.10
P1	2.00+/-0.05
K0	1.15min/1.45max
T	0.254+/-0.13

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